Abstracts

Chip Level IMPATT Combining at 40 GHz (1981 [MWSYM])

C.T. Rucker, J.W. Amoss and G.N. Hill. "Chip Level IMPATT Combining at 40 GHz (1981 [MWSYM])." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 347-348.

Results with series and series-parallel connections of CW40 GHz GaAs IMPATT diodes are discussed. The multichip geometries utilize Raytheon CW double-drift device chips and are essentially scaled versions of successful X-band geometries reported previously. Maximum series combining efficiency of 82 percent has been achieved.

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